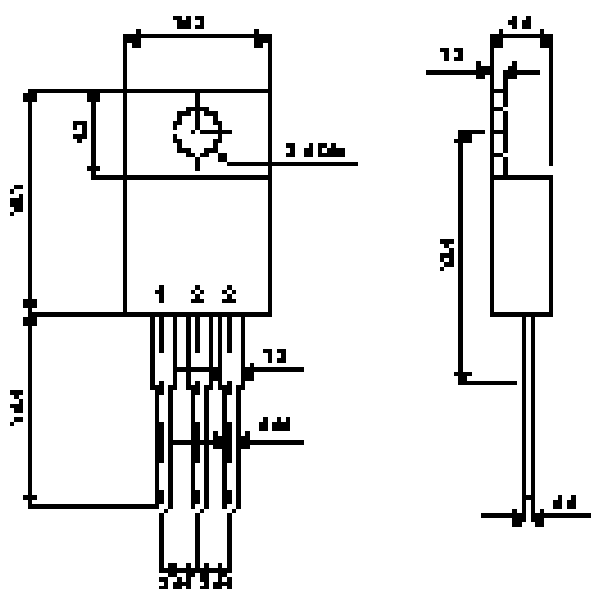


MECHANICAL DATA

Dimensions in mm



TO220

Pin 1 – Base Pad 2 – Collector Pad 3 – Emitter

NPN FAST SWITCHING TRANSISTOR

FEATURES

- LOW SATURATION VOLTAGE
- ULTRA FAST TURN-ON AND TURN-OFF SWITCHING ($t_r / t_f = 40\text{ns}$)

APPLICATIONS

- High speed TO220 transistor suited for low voltage applications.
- High frequency and high efficiency converters, switching regulators and motor controls.
- Ideally suited for 12V and 24V inverters.

ABSOLUTE MAXIMUM RATINGS ($T_{\text{case}} = 25^\circ\text{C}$ unless otherwise stated)

V_{CBO}	Collector – Base Voltage	200V
V_{CEO}	Collector – Emitter Voltage ($I_B = 0$)	100V
V_{EBO}	Emitter – Base Voltage ($I_C = 0$)	7V
I_C	Collector Current	14A
I_B	Base Current	4A
P_{tot}	Total Dissipation at $T_{\text{case}} = 25^\circ\text{C}$	85W
T_{stg}	Storage Temperature Range	-55 to 175°C
R_{th}	Thermal Resistance Junction – Case	175°C/W



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ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
ELECTRICAL CHARACTERISTICS						
$V_{CEO(sus)*}$ Collector – Emitter Sustaining Voltage	$I_C = 200mA$	100			V	
$V_{(BR)EBO*}$ Emitter – Base Breakdown Voltage	$I_E = 1mA$	7				
I_{CER*} Collector Cut-Off Current	$I_B = 0$ $R_{BE} = 50\Omega$	$V_{CE} = 200V$ $T_C = 125^{\circ}C$		3	mA	
I_{CBO*} Collector – Base Cut-Off Current	$I_E = 0$ $V_{BE} = -1.5V$	$V_{CB} = 200V$ $T_C = 125^{\circ}C$		1	mA	
I_{EBO*} Emitter Cut-Off Current	$I_C = 0$	$V_{EB} = 5V$		1	mA	
$V_{CE(sat)*}$ Collector – Emitter Saturation Voltage	$I_C = 5A$	$I_B = 500mA$		0.6	V	
	$I_C = 10A$	$I_B = 1A$		1.5		
$V_{BE(sat)*}$ Base – Emitter Saturation Voltage	$I_C = 10A$	$I_B = 1A$		2	V	
SWITCHING CHARACTERISTICS (resistive load)						
t_{on} Turn-On Time	$V_{CC} = 50V$	$I_C = 12A$		0.2	0.6	μS
t_s Storage Time	$V_{BE} = -6V$	$I_{B1} = 1.2A$		0.4	1	
t_f Fall Time	$R_{BB} = 2.5\Omega$			0.04	0.25	
SWITCHING CHARACTERISTICS (inductive load)						
t_s Storage Time	$V_{CC} = 50V$ $V_{BE} = -5V$ $L_B = 0.5\mu H$	$I_C = 12A$ $I_{B1} = 1.2A$		0.5		μS
t_f Fall Time				0.04		
t_s Storage Time ($T_j = 125^{\circ}C$)					2	
t_f Fall Time ($T_j = 125^{\circ}C$)					0.15	

* Pulse test $t_p = 300\mu s$, $\delta \leq 2\%$